



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors

Mechanical Data

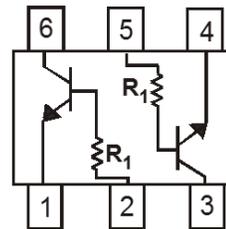
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (Approximate)

R1 (NOM)
4.7k Ω

SOT363



Top View



Device Schematic

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

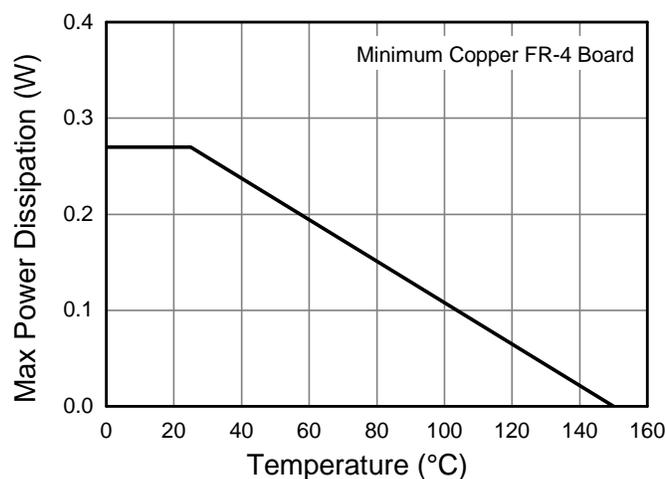
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C (Max)	100	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

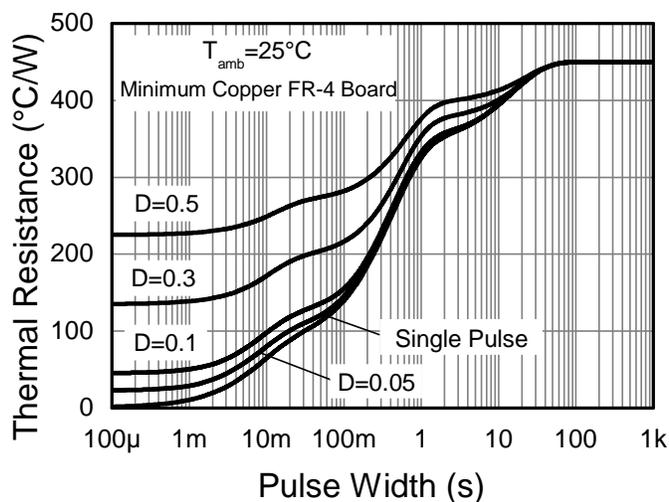
Characteristic	Symbol	Value	Unit
Power Dissipation (Notes 5 & 6)	P_D	270	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	450	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Mounted on FR-4 PC Board with minimum recommended pad layout.
 6. 150mW per element must not be exceeded.

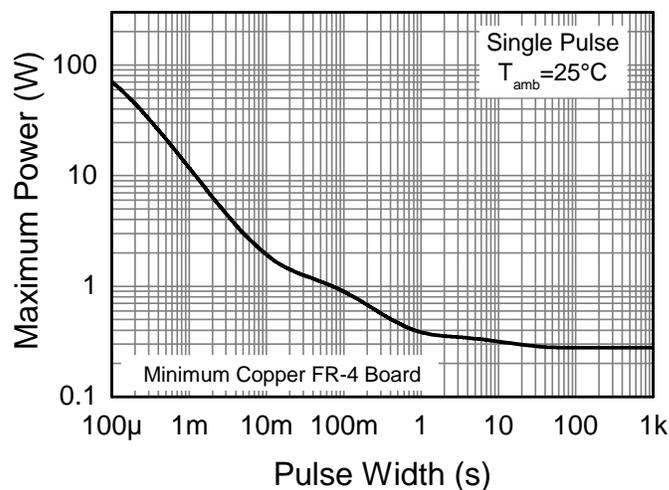
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance



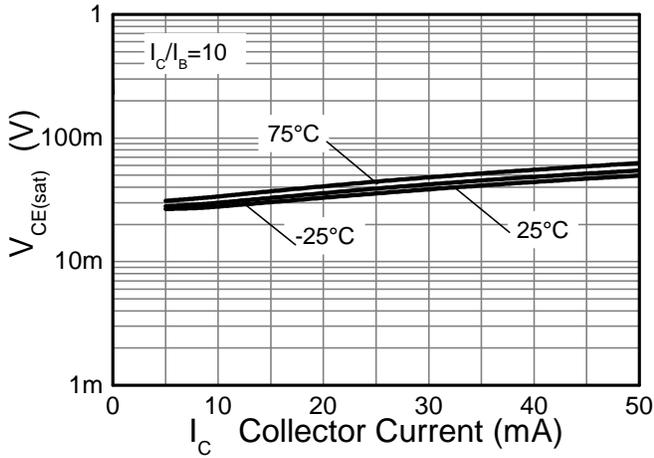
Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

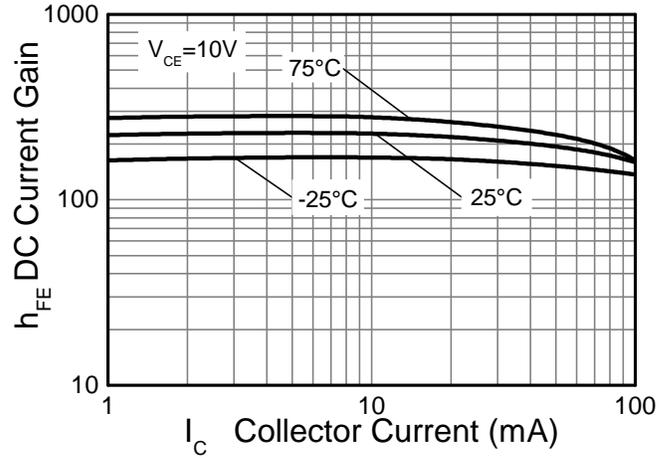
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	$I_C = 50\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CEO}	50	—	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	$I_E = 50\mu\text{A}$
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 50\text{V}$
Emitter Cutoff Current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C/I_B = 2.5\text{mA} / 0.25\text{mA}$
DC Current Transfer Ratio	h_{FE}	100	250	600	—	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$
Input Resistor (R_1) Tolerance	ΔR_1	-30	—	+30	%	—
Gain-Bandwidth Product (Note 7)	f_T	—	250	—	MHz	$V_{CE} = 10\text{V}, I_E = -5\text{mA}, f = 100\text{MHz}$

Note: 7. Transistor - For Reference Only.

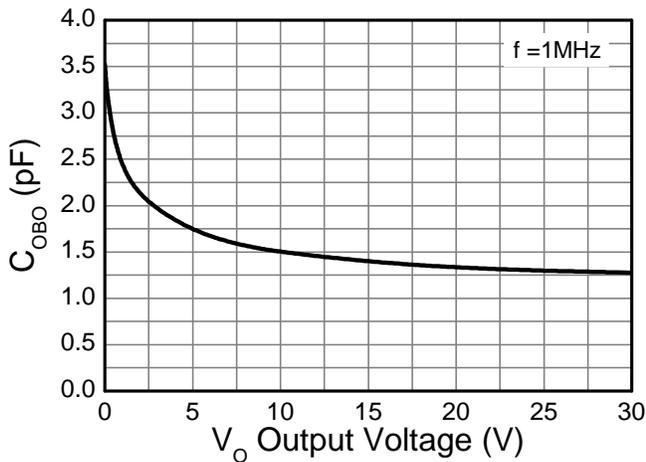
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



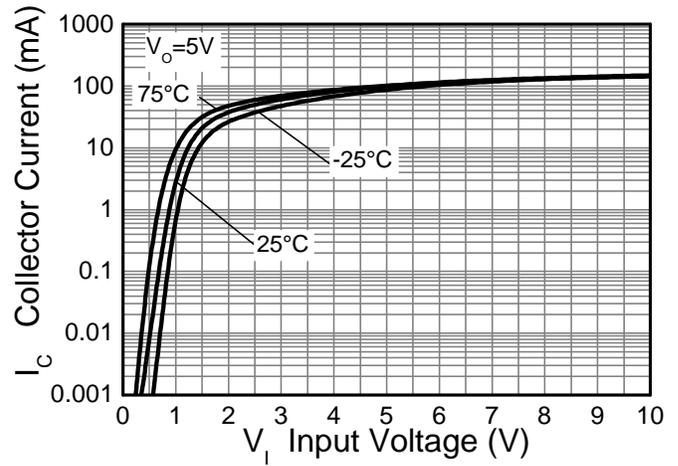
V_{CE(sat)} vs. I_C



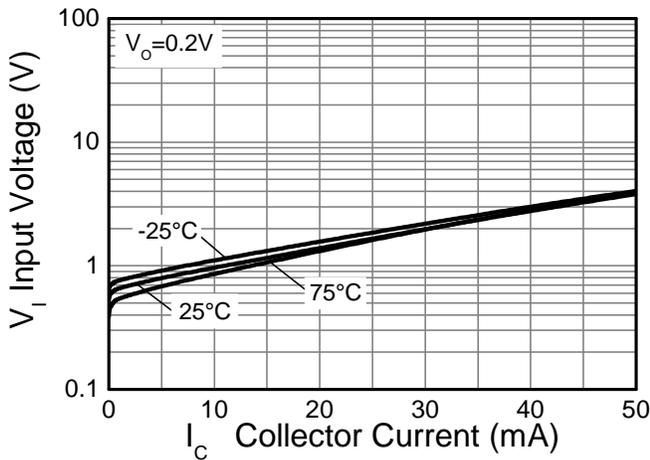
h_{FE} vs I_C



C_{OBO} vs V_O



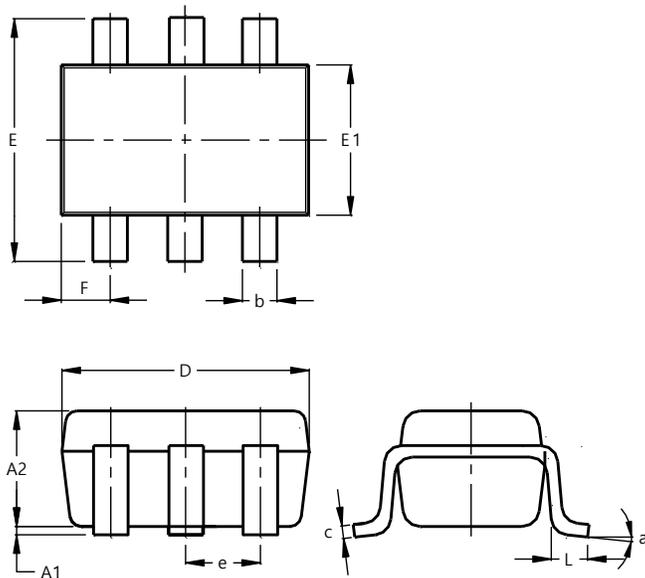
I_C vs V_I



V_I vs I_C

Package Outline Dimensions

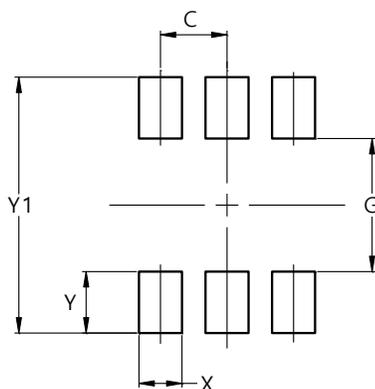
SOT363



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500